

# **N-channel SiC power MOSFET**

V <sub>DSS</sub>	750V
R <sub>DS(on)</sub> (Typ.)	26mΩ
$I_{D}^{^{*1}}$	51A
$P_D$	150W

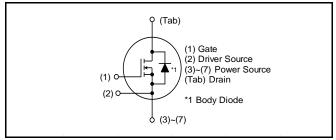
## Outline



#### Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

#### •Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

# Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- · Induction heating
- Motor drives

# Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Typo	Tape width (mm)	24
Type	Basic ordering unit (pcs)	1000
	Taping code	TL
	Marking	SCT4026DW7

# ● **Absolute maximum ratings** (T<sub>vi</sub> = 25°C unless otherwise specified.)

Parameter		Symbol	Value	Unit	
Drain - source voltage		$V_{DSS}$	750	V	
Continuous drain	$V_{GS} = V_{GS\_on}$	$T_c = 25^{\circ}C$	I <sub>D</sub> , I <sub>S</sub> *1	51	А
and source current	V <sub>GS</sub> = V <sub>GS_on</sub>	$T_c = 100$ °C	I <sub>D</sub> , I <sub>S</sub>	36	Α
Pulsed drain current	$V_{GS} = V_{GS\_on}$	$T_c = 25^{\circ}C$	l <sub>D,pulse</sub> *2	91	Α
Body diode pulsed forward	ard current	$T_c = 25^{\circ}C$	I <sub>S,pulse</sub> *1,*3	51	Α
Body diode surge forward current		$V_{GS} = 0 V$	I <sub>S,pulse</sub> *1,*4	91	Α
Gate - source voltage (DC)		$V_{GSS\_DC}$	-4 to +21	V	
Gate - source surge voltage (t <sub>surge</sub> < 300ns)		$V_{GSS\_surge}^{*5}$	-4 to +23	V	
Recommended turn-on gate - source drive voltage		ive voltage	$V_{GS\_on}^{*6}$	+15 to +18	V
Recommended turn-off gate - source drive voltage		$V_{GS\_off}$	0	V	
Virtual junction temperature		$T_{vj}$	175	°C	
Range of storage temperature		$T_{stg}$	-40 to +175	°C	

# ullet Electrical characteristics (T<sub>vj</sub> = 25°C unless otherwise specified)

Parameter	Cymbol	Conditions	Values			Unit
raiailletei			Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	W	$V_{GS} = 0 \text{ V}, I_D = 9.2 \text{mA}$				V
	V (BR)DSS	$T_{vj} = 25^{\circ}C$	750	-	-	V
		$V_{GS} = 0 \text{ V}, V_{DS} = 750 \text{V}$				
Zero Gate voltage Drain current	I <sub>DSS</sub>	$T_{vj} = 25^{\circ}C$	-	1	80	μA
Diam ourion		T <sub>vj</sub> = 150°C	-	10	-	
Gate - Source leakage current	I <sub>GSS+</sub>	$V_{GS} = +21V , V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I <sub>GSS-</sub>	$V_{GS} = -4V$ , $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_{D} = 15.4 \text{mA}$	2.8	-	4.8	V
		$V_{GS} = 18V, I_{D} = 29A$				_
Static Drain - Source on - state resistance	R <sub>DS(on)</sub> *8	$T_{vj} = 25^{\circ}C$	-	26	34	mΩ
2 2		T <sub>vj</sub> = 150°C	-	44	-	
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	1	-	Ω

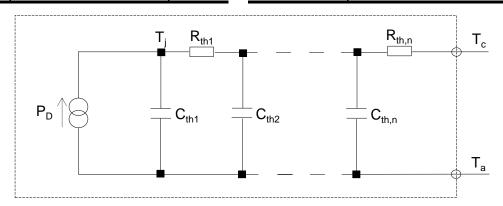
# ●Thermal resistance

Parameter	Symbol	Values			Unit
Falametei		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R <sub>thJC</sub> *9	-	0.79	1.0	K/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	5.1 ×10 <sup>-2</sup>	
R <sub>th2</sub>	3.6 ×10 <sup>-1</sup>	K/W
R <sub>th3</sub>	3.8 ×10 <sup>-1</sup>	

Symbol	Value	Unit
C <sub>th1</sub>	8.8 ×10 <sup>-4</sup>	
C <sub>th2</sub>	4.5 <b>×</b> 10 <sup>-3</sup>	Ws/K
C <sub>th3</sub>	1.3 ×10 <sup>-1</sup>	



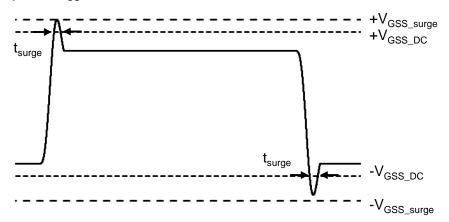
# ullet Electrical characteristics (T<sub>vj</sub> = 25°C unless otherwise specified)

Darameter	Symbol Conditions -	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	<b>g</b> fs *8	$V_{DS} = 10V, I_{D} = 29A$	-	16	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0V$	1	2320	1	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 500V	1	111	ı	pF
Reverse transfer capacitance	$C_{rss}$	f = 1MHz	•	9	•	
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	ı	143	1	pF
Total Gate charge	Q <sub>g</sub> *8	$V_{DS} = 500V$ $I_{D} = 29A$	1	94	ı	
Gate - Source charge	Q <sub>gs</sub> *8	$V_{GS} = 18V$	ı	20	ı	nC
Gate - Drain charge	Q <sub>gd</sub> *8	See Fig. 1-1, 1-2.	-	23	-	
Turn - on delay time	t <sub>d(on)</sub> *8	$V_{DS} = 500V$	ı	9.5	ı	
Rise time	t <sub>r</sub> *8	$I_D = 29A$ $V_{GS} = +18V / 0V$	ı	22	ı	ns
Turn - off delay time	t <sub>d(off)</sub> *8	$R_G = 6.8\Omega$ , L = 250µH $E_{on}$ includes diode	ı	45	ı	113
Fall time	t <sub>f</sub> *8	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	ı	13	ı	
Turn - on switching loss	E <sub>on</sub> *8	See Fig. 2-1, 2-2, 2-3.	-	213	-	1
Turn - off switching loss	E <sub>off</sub> *8		-	73	-	μJ

# ●Body diode electrical characteristics (Source-Drain) (T<sub>vi</sub> = 25°C unless otherwise specified)

Darameter	Symbol	Conditions	Values			Unit
Parameter	Symbol Conditions –	Min.	Тур.	Max.	Offic	
Forward voltage	V <sub>SD</sub> *8	$V_{GS} = 0V, I_{S} = 29A$	ı	3.3	ı	V
Reverse recovery time	t <sub>rr</sub> *8	$I_F = 29A$ $V_R = 500V$	ı	12	ı	ns
Reverse recovery charge	Q <sub>rr</sub> *8	di/dt = 2700A/µs	ı	141	ı	nC
Peak reverse recovery current	I <sub>rrm</sub> *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	24	-	А

- \*1 Limited by maximum  $T_{vj}$  and for Max.  $R_{thJC}$ .
- \*2 Pulse width and duty cycle are limited by T<sub>vj,max</sub>.
- \*3 Only for body-diode, Repititive pulse, PW ≤ 1.5µs, Duty cycle ≤ 5%
- \*4 When used as a protective function, PW ≤ 10µs
- \*5 Example of acceptable V<sub>GS</sub> waveform



Please note especially when using driver source that V<sub>GSS\_surge</sub> must be in the range of absolute maximum rating.

- \*6 Please be advised not to use SiC-MOSFETs with V<sub>GS</sub> below 10V as doing so may cause thermal runaway.
- \*7 Tested after applying  $V_{GS} = 21V$  for 100ms.
- \*8 Pulsed
- \*9 Measured conformable to JESD51-14.

See the application note "rthjc\_measurement\_and\_usage\_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc\_measurement\_and\_usage\_an-e.pdf

Fig.1 Power Dissipation Derating Curve

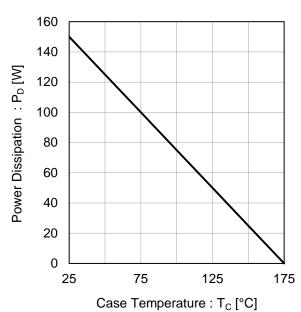


Fig.2 Maximum Safe Operating Area

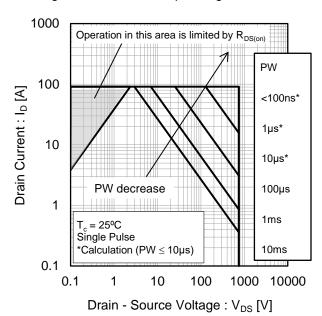
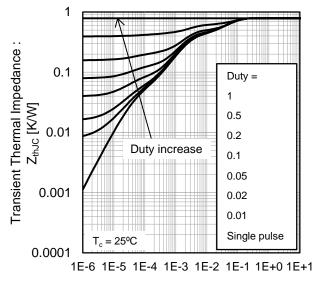
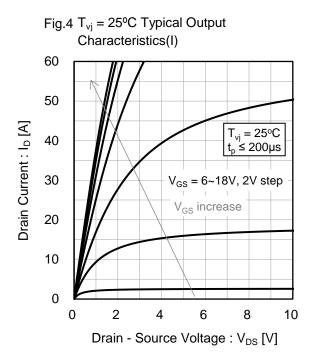


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



Pulse Width: PW [s]



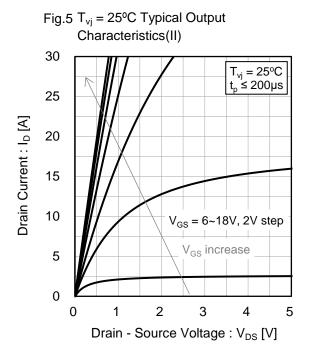
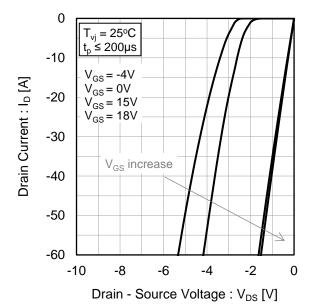
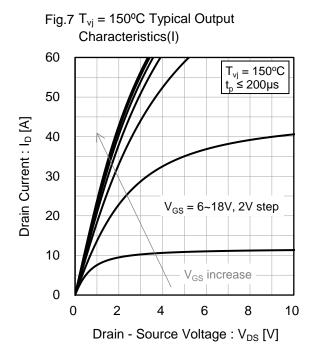
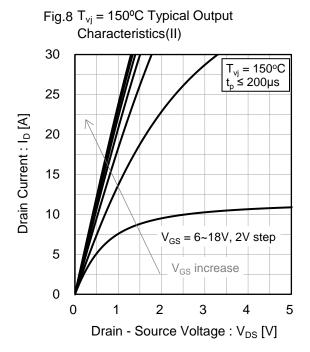
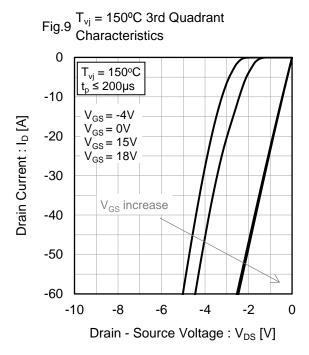


Fig.6  $T_{vj}$  = 25°C 3rd Quadrant Characteristics









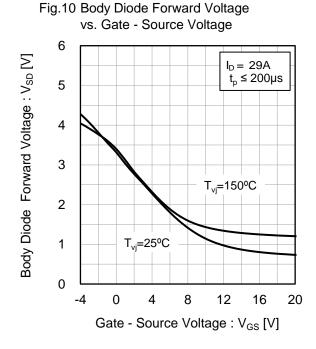


Fig.11 Typical Transfer Characteristics (I)

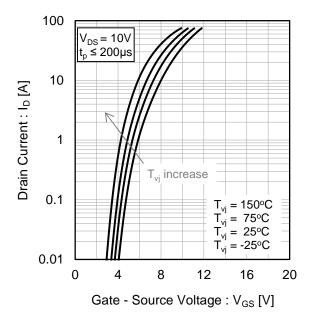


Fig.12 Typical Transfer Characteristics (II)

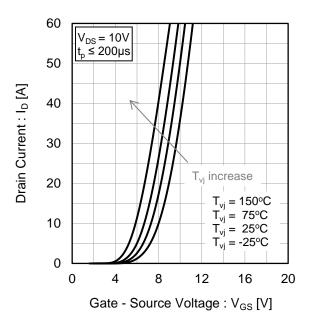


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

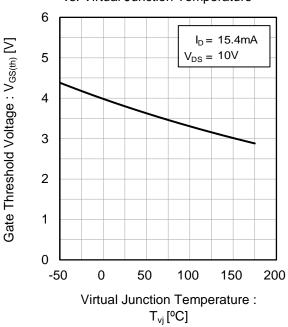
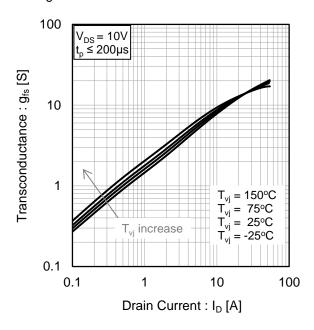
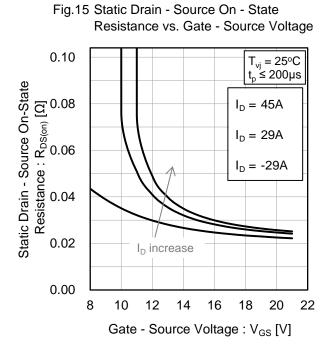


Fig.14 Transconductance vs. Drain Current

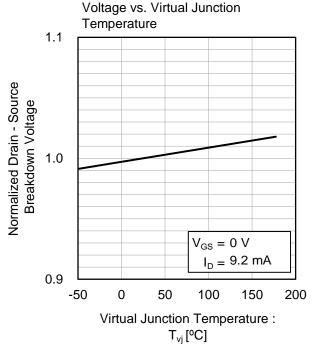




Resistance vs. Virtual Junction Temperature 0.10 V<sub>GS</sub> = 18V t<sub>p</sub> ≤ 200µs Static Drain - Source On-State Resistance :  $R_{DS(on)}$   $[\Omega]$  80.0 90.0 90.0  $I_D = 45A$ = 29A $I_{D} = -29A$ 0.02  $I_D$  increase 0.00 -50 100 0 50 150 200 Virtual Junction Temperature: T<sub>vi</sub> [°C]

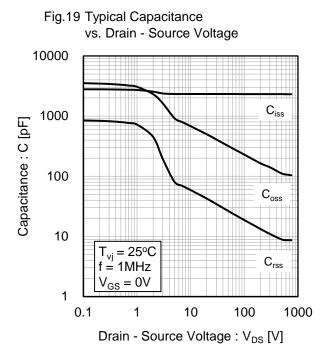
Fig.16 Static Drain - Source On - State

Fig.17 Static Drain - Source On - State



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Fig.18 Normalized Drain - Source Breakdown



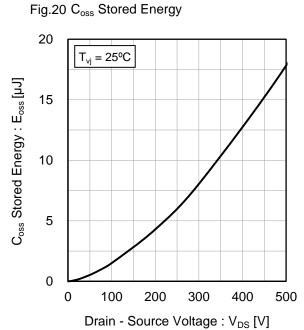


Fig.21 Dynamic Input Characteristics

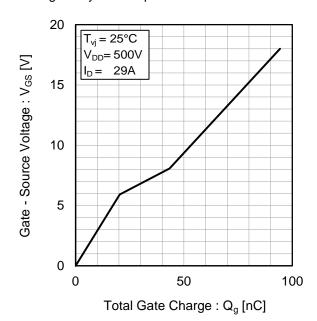


Fig.22 Typical Switching Time

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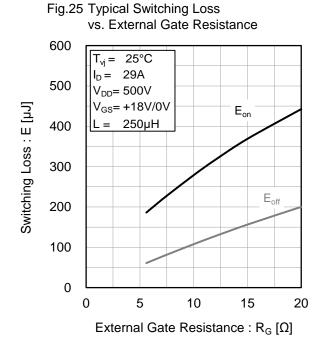
10

External Gate Resistance :  $R_G[\Omega]$ 

vs. Drain - Source Voltage 600  $T_{vi} = 25^{\circ}C$ 29A 500  $V_{GS} = +18V/0V$ Switching Loss: E [µJ]  $R_G = 6.8\Omega$ 400  $L = 250 \mu H$ 300 200 100 0 200 100 300 400 500 Drain - Source Voltage: V<sub>DS</sub> [V]

Fig.23 Typical Switching Loss

Fig.24 Typical Switching Loss vs. Drain Current 600 25°C  $V_{DD} = 500V$ 500  $V_{GS}$ = +18V/0V  $R_G = 6.8\Omega$ Switching Loss : E [µJ] 250µH L= 400  $\mathsf{E}_{\mathsf{on}}$ 300 200  $\mathsf{E}_{\mathsf{off}}$ 100 0 0 10 20 30 40 50 60 Drain Current: I<sub>D</sub> [A]



20

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### • Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

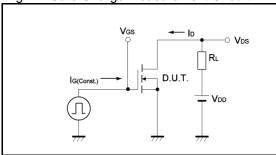


Fig.2-1 Switching Characteristics Measurement Circuit

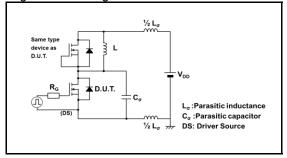


Fig.2-3 Waveforms for Switching Energy Loss

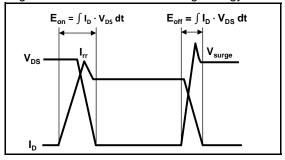


Fig.3-1 Reverse Recovery Time Measurement Circuit

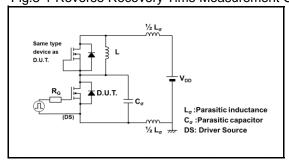


Fig.1-2 Gate Charge Waveform

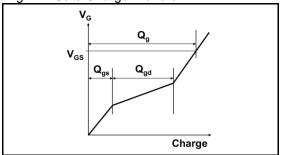


Fig.2-2 Waveforms for Switching Time

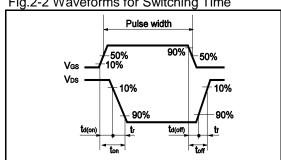
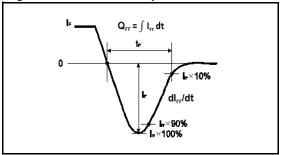
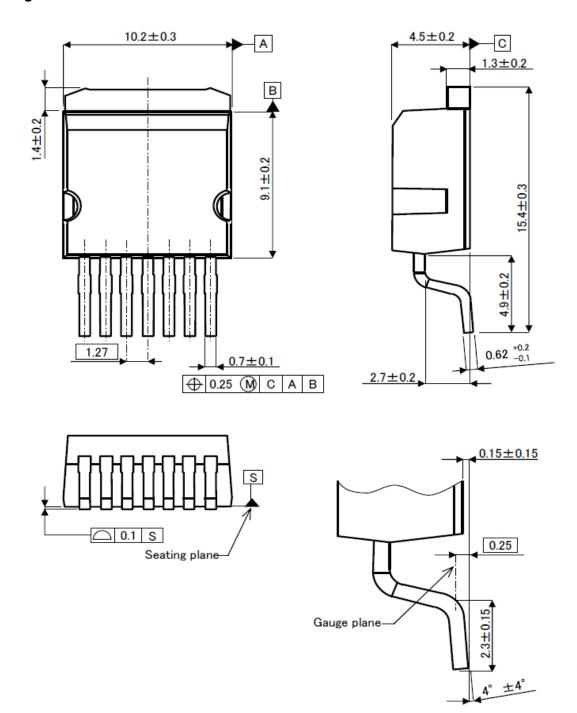


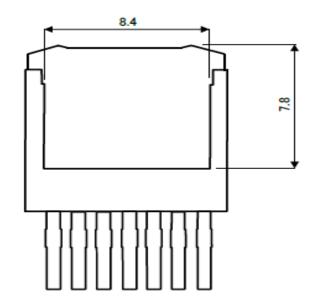
Fig.3-2 Reverse Recovery Waveform



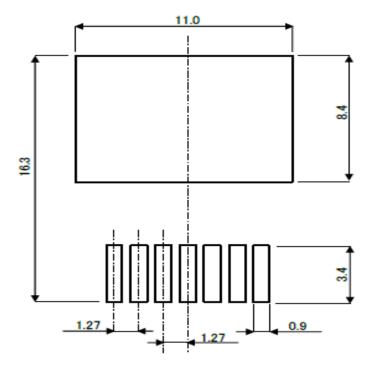
# ●Package Dimensions



Unit: mm



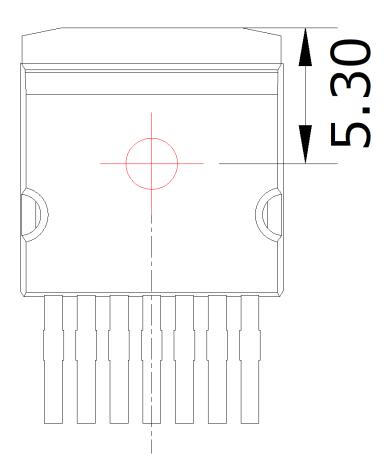
# RECOMMENDED FOOTPRINT DIMENSIONS



Unit: mm

# ●Die Bonding Layout





- •Front view of the packaging.
- •Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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